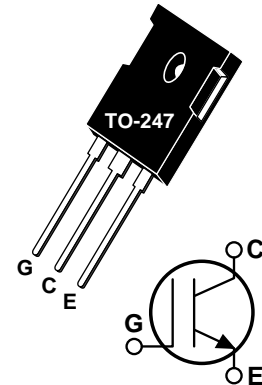


Thunderbolt IGBT™

The Thunderbolt IGBT™ is a new generation of high voltage power IGBTs. Using Non-Punch Through Technology the Thunderbolt IGBT™ offers superior ruggedness and ultrafast switching speed.

- Low Forward Voltage Drop
- Low Tail Current
- Avalanche Rated
- High Freq. Switching to 150KHz
- Ultra Low Leakage Current
- RBSOA and SCSOA Rated




MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT40GT60BR	UNIT
V_{CES}	Collector-Emitter Voltage	600	Volts
V_{CGR}	Collector-Gate Voltage ($R_{GE} = 20K\Omega$)	600	
V_{EC}	Emitter-Collector Voltage	15	
V_{GE}	Gate-Emitter Voltage	± 20	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	80	Amps
I_{C2}	Continuous Collector Current @ $T_C = 105^\circ\text{C}$	40	
I_{CM}	Pulsed Collector Current ^① @ $T_C = 25^\circ\text{C}$	160	
I_{LM}	RBSOA Clamped Inductive Load Current @ $R_g = 11\Omega$ $T_C = 125^\circ\text{C}$	80	
E_{AS}	Single Pulse Avalanche Energy ^②	40	mJ
P_D	Total Power Dissipation	345	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{CES}	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 0.5mA$)	600			Volts
RBV_{CES}	Collector-Emitter Reverse Breakdown Voltage ($V_{GE} = 0V, I_C = 100mA$)	-15			
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 500\mu A, T_j = 25^\circ\text{C}$)	3	4	5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = I_{C2}, T_j = 25^\circ\text{C}$)	1.6	2.15	2.5	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = I_{C2}, T_j = 125^\circ\text{C}$)			2.8	
I_{CES}	Collector Cut-off Current ($V_{CE} = V_{CES}, V_{GE} = 0V, T_j = 25^\circ\text{C}$)			80	μA
	Collector Cut-off Current ($V_{CE} = V_{CES}, V_{GE} = 0V, T_j = 125^\circ\text{C}$)			2000	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V, V_{CE} = 0V$)			± 100	nA

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

APT40GT60BR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1 \text{ MHz}$		2190	2520	pF
C_{oes}	Output Capacitance			220	320	
C_{res}	Reverse Transfer Capacitance			130	220	
Q_g	Total Gate Charge ^③	Gate Charge $V_{GE} = 15V$ $V_{CC} = 0.5V_{CES}$ $I_C = I_{C2}$		200	300	nC
Q_{ge}	Gate-Emitter Charge			12	20	
Q_{gc}	Gate-Collector ("Miller") Charge			86	130	
$t_d(\text{on})$	Turn-on Delay Time	Resistive Switching (25°C) $V_{GE} = 15V$ $V_{CC} = 0.5V_{CES}$ $I_C = I_{C2}$ $R_G = 10\Omega$		13	30	ns
t_r	Rise Time			53	110	
$t_d(\text{off})$	Turn-off Delay Time			205	310	
t_f	Fall Time			250	500	
$t_d(\text{on})$	Turn-on Delay Time	Inductive Switching (150°C) $V_{CLAMP(\text{Peak})} = 0.66V_{CES}$ $V_{GE} = 15V$ $I_C = I_{C2}$ $R_G = 10\Omega$ $T_J = +150^\circ\text{C}$		20	40	ns
t_r	Rise Time			43	90	
$t_d(\text{off})$	Turn-off Delay Time			295	440	
t_f	Fall Time			58	120	
E_{on}	Turn-on Switching Energy	$R_G = 10\Omega$ $T_J = +150^\circ\text{C}$.85	2	mJ
E_{off}	Turn-off Switching Energy			1.5	3	
E_{ts}	Total Switching Losses			2.3	5	
$t_d(\text{on})$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CLAMP(\text{Peak})} = 0.66V_{CES}$ $V_{GE} = 15V$ $I_C = I_{C2}$ $R_G = 10\Omega$ $T_J = +25^\circ\text{C}$		20	40	ns
t_r	Rise Time			46	90	
$t_d(\text{off})$	Turn-off Delay Time			265	400	
t_f	Fall Time			53	110	
E_{ts}	Total Switching Losses			1.75	4	mJ
g_{fe}	Forward Transconductance	$V_{CE} = 20V, I_C = I_{C2}$	4			S

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.36	°C/W
$R_{\theta JA}$	Junction to Ambient			40	
W_T	Package Weight		0.22		oz
			6.1		gm
Torque	Mounting Torque (using a 6-32 or 3mm Binding Head Machine Screw)			10	lb•in
				1.1	N•m

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② $I_C = I_{C2}, R_{GE} = 25\Omega, L = 50\mu\text{H}, T_J = 25^\circ\text{C}$

③ See MIL-STD-750 Method 3471

APT Reserves the right to change, without notice, the specifications and information contained herein.

APT40GT60BR

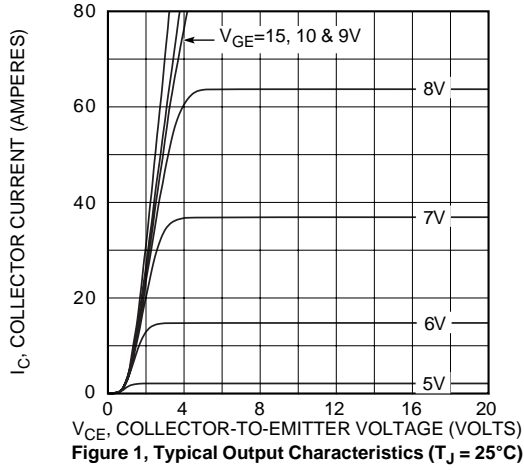


Figure 1, Typical Output Characteristics ($T_J = 25^\circ\text{C}$)

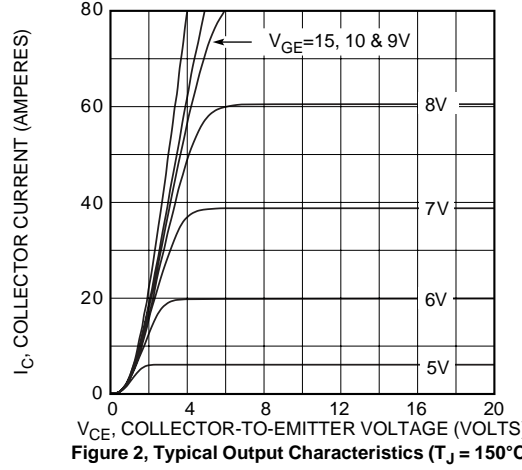


Figure 2, Typical Output Characteristics ($T_J = 150^\circ\text{C}$)

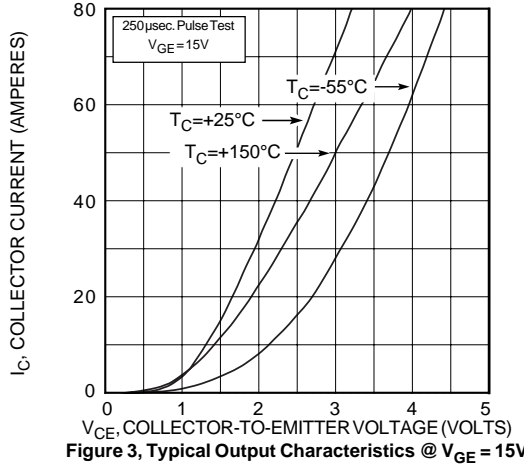


Figure 3, Typical Output Characteristics @ $V_{GE} = 15\text{V}$

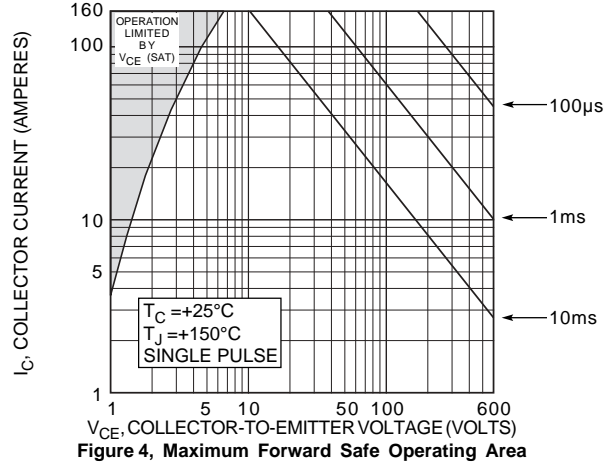


Figure 4, Maximum Forward Safe Operating Area

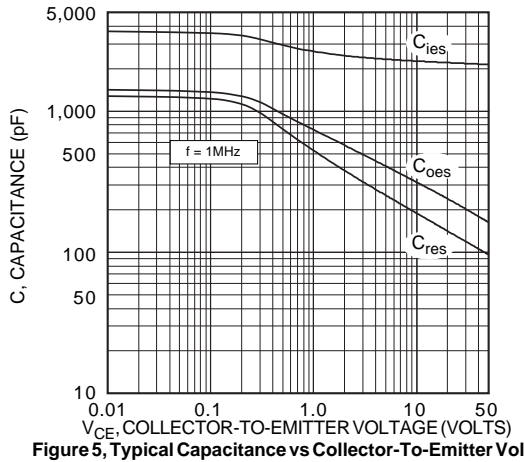


Figure 5, Typical Capacitance vs Collector-To-Emitter Voltage

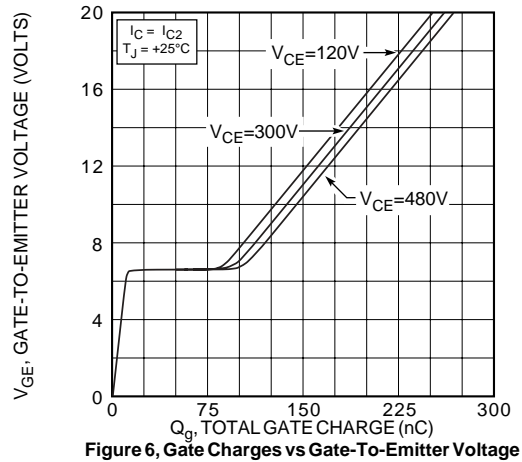


Figure 6, Gate Charges vs Gate-To-Emitter Voltage

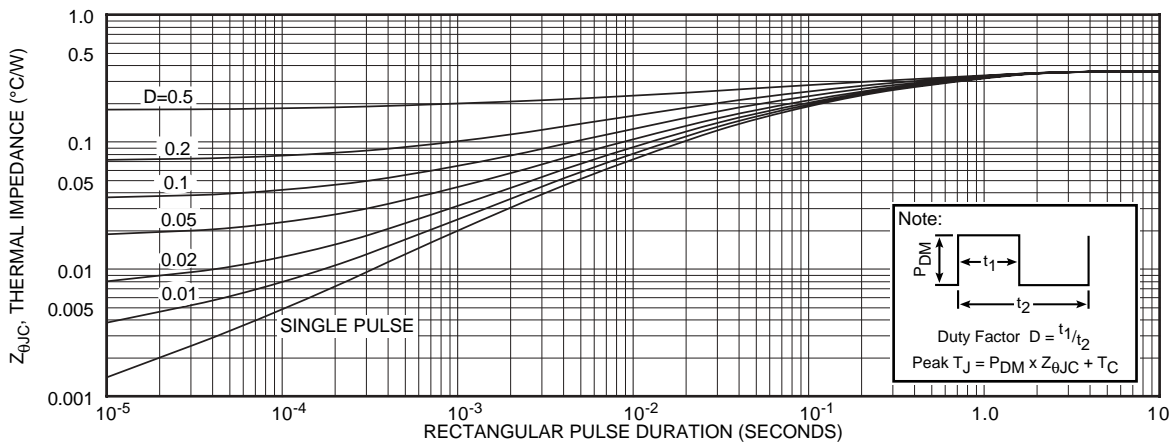


Figure 7, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

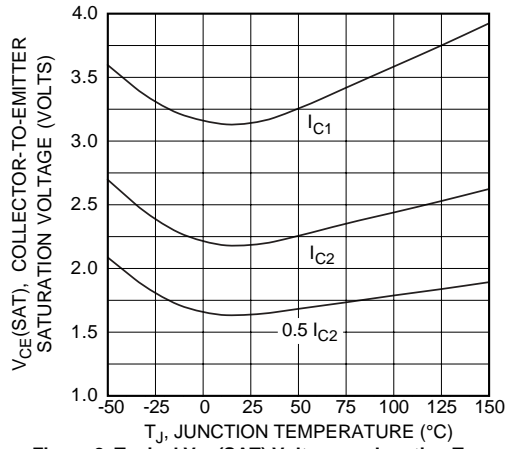


Figure 8, Typical $V_{CE(SAT)}$ Voltage vs Junction Temperature

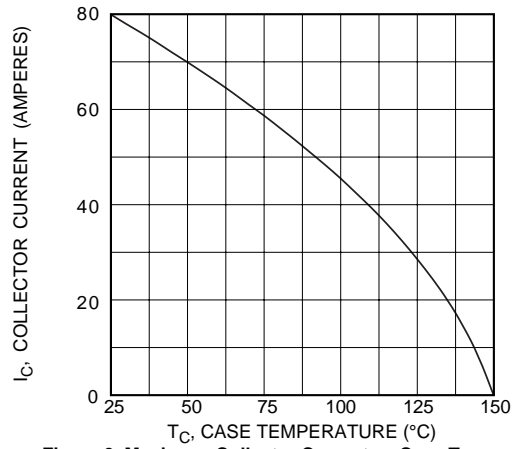


Figure 9, Maximum Collector Current vs Case Temperature

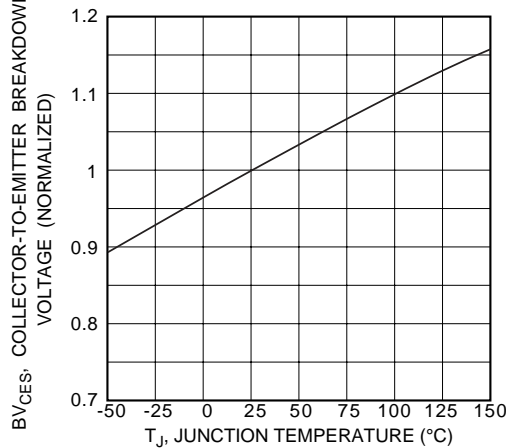


Figure 10, Breakdown Voltage vs Junction Temperature

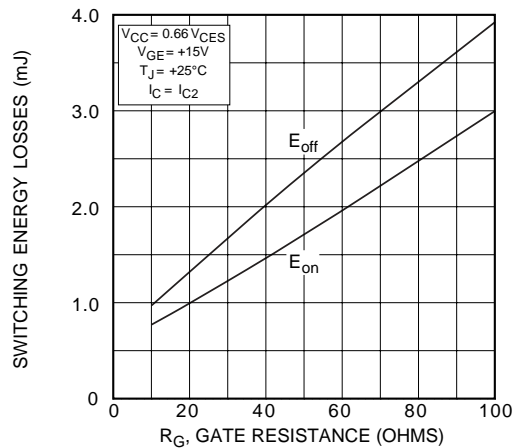


Figure 11, Typical Switching Energy Losses vs Gate Resistance

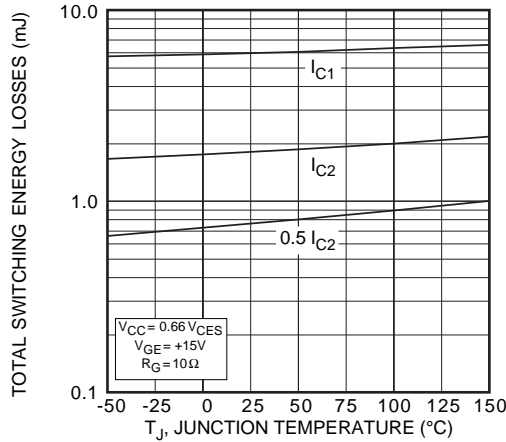


Figure 12, Typical Switching Energy Losses vs. Junction Temperature

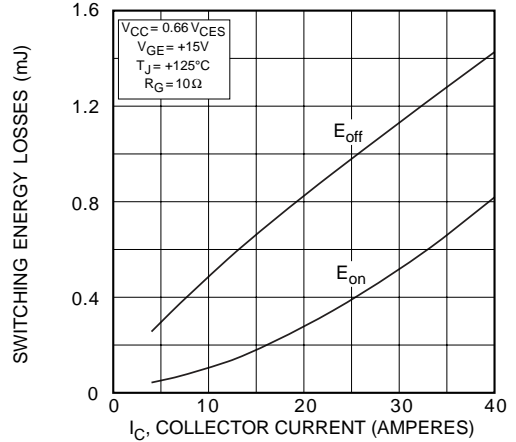


Figure 13, Typical Switching Energy Losses vs Collector Current

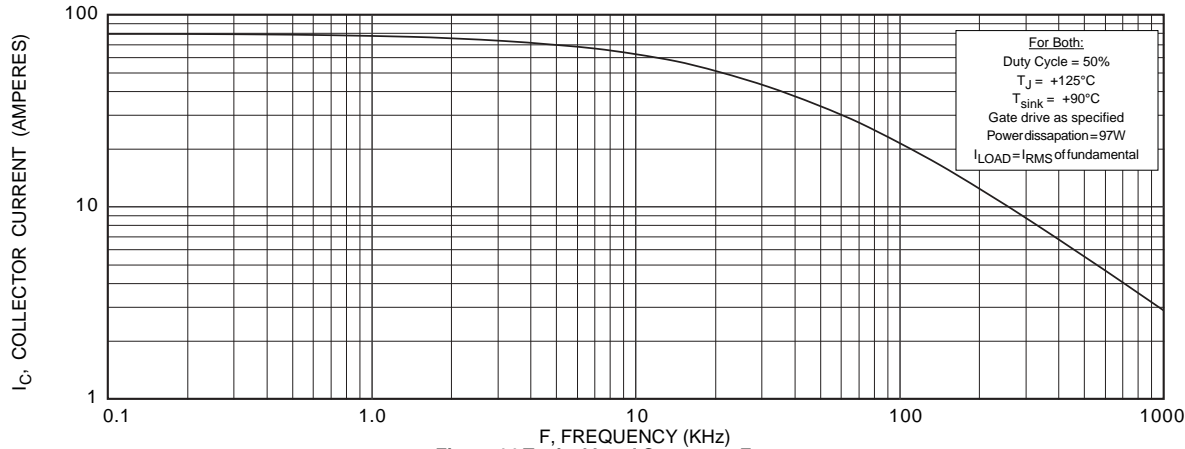


Figure 14, Typical Load Current vs Frequency

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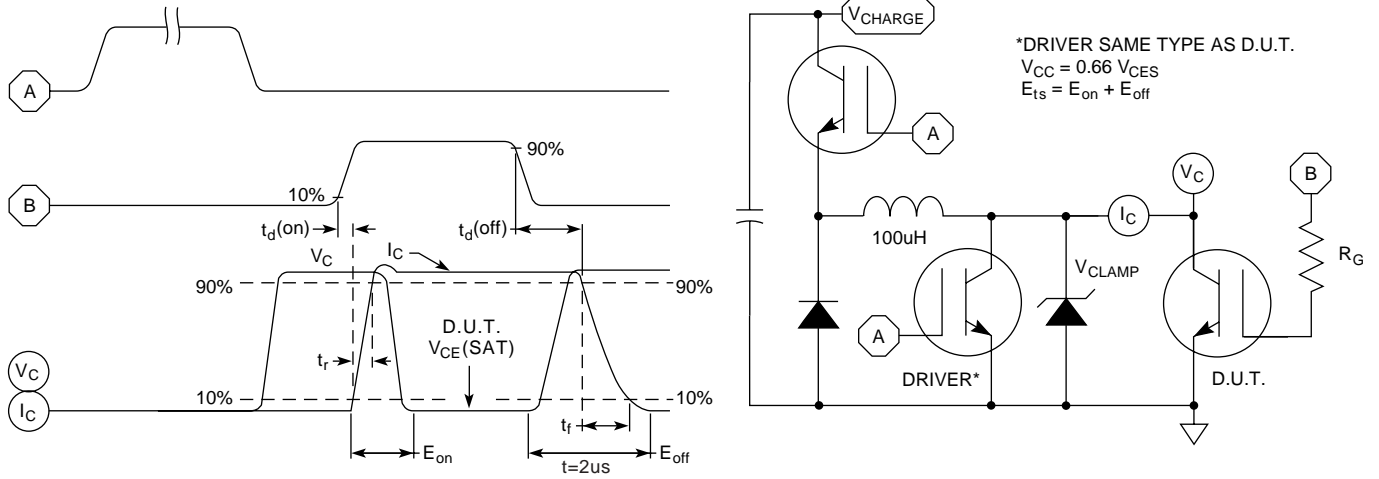


Figure 15, Switching Loss Test Circuit and Waveforms

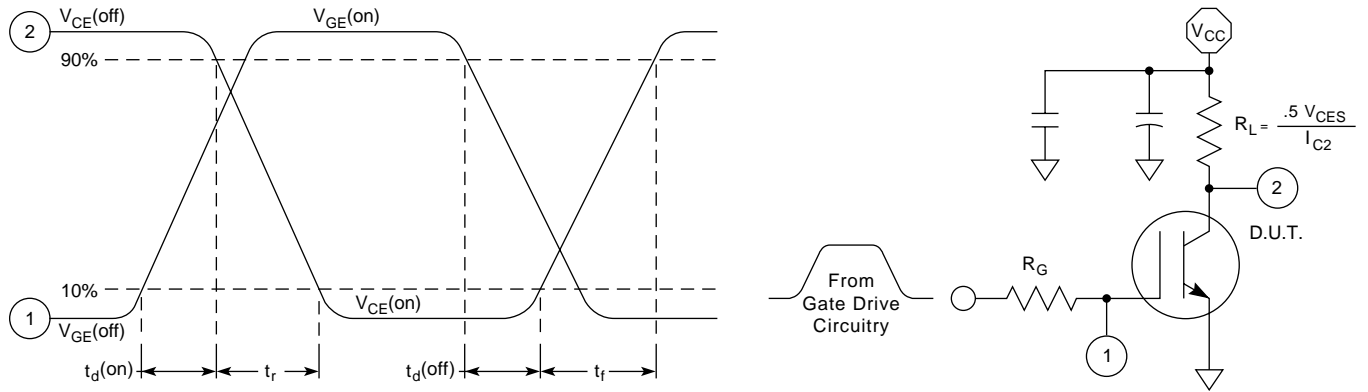
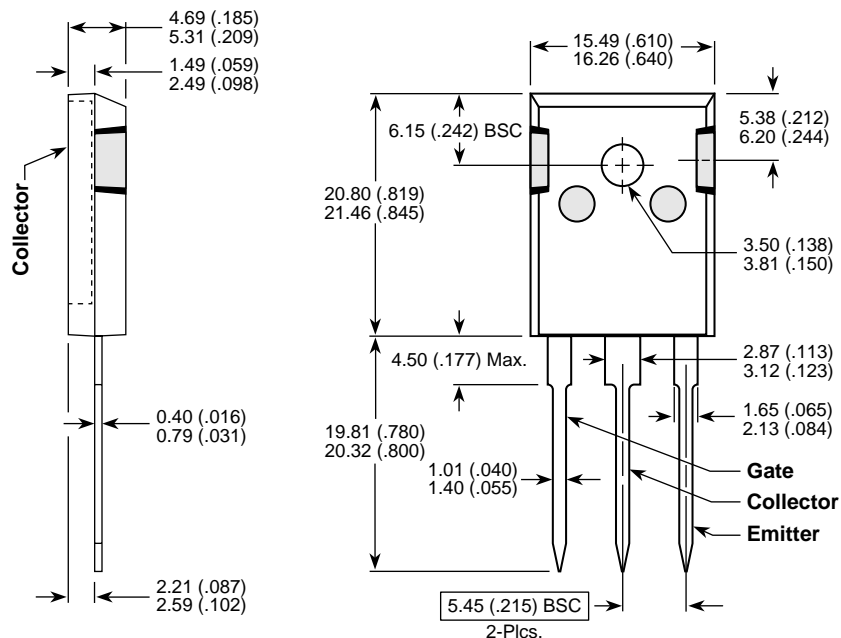


Figure 16, Resistive Switching Time Test Circuit and Waveforms

T0-247 Package Outline



Dimensions in Millimeters and (Inches)